

FMMT459

500V NPN HIGH VOLTAGE TRANSISTOR IN SOT23

Feature

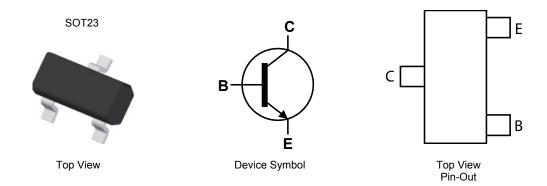
- BV_{CFV} > 500V
- BV_{ECV} > 6V reverse blocking
- I_C = 150mA high Continuous Collector Current
- I_{CM} Up to 500mA Peak Pulse Current
- 625mW Power Dissipation
- Low Saturation Voltage <-90mV @ 50mA
- Excellent h_{FE} Characteristics Up To 120mA
- Complementary PNP Type: FMMT559
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight 0.008 grams (approximate)

Applications

- Off-line switching applications
- RCD circuits
- PFC disable switch in PSU
- Emergency lighting
- Piezo actuators
- Telecom protected line switching



Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT459TA	AEC-Q101	459	7	8	3,000
FMMT459QTA	Automotive	459	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information







Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	500	V
Collector-Emitter Voltage	V _{CEV}	500	V
Collector-Emitter Voltage	V _{CEO}	450	V
Emitter-Base Voltage	V _{EBO}	7	V
Emitter-Collector Voltage	V _{ECV}	6	V
Continuous Collector Current	Ic	150	mA
Peak Pulse Current	I _{CM}	500	mA
Base Current	I _B	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

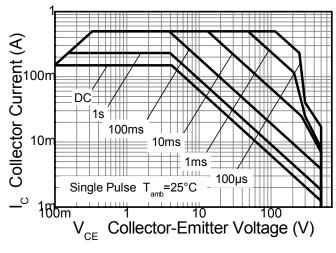
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

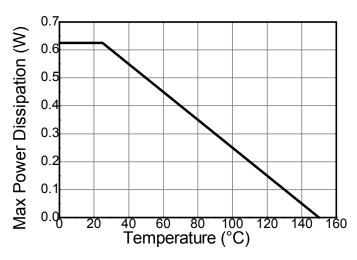
Notes:

^{6.} For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured 6. For a device surface modified on 25mm x 25mm FR4 PCB with high coverage of when operating in a steady-state condition.
7. Same as note 6, except the device is measured at t ≤ 5 sec.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



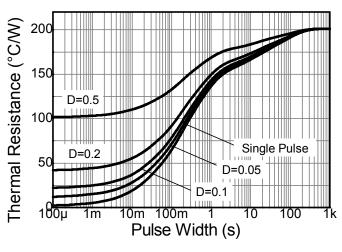
Thermal Characteristics and Derating Information

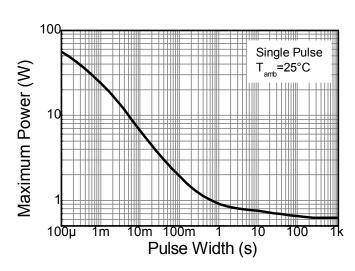




Safe Operating Area

Derating Curve

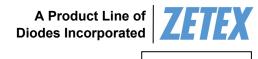




Transient Thermal Impedance

Pulse Power Dissipation





FMMT459

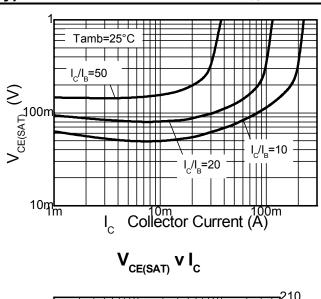
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

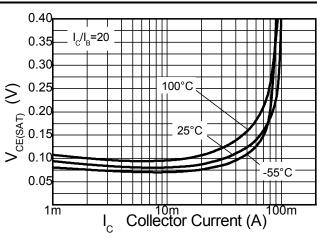
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	500	700	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	500	700	_	V	$I_C = 10\mu A$; 0.3V > V_{BE} > -1V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	450	500	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.1	_	V	$I_{E} = 100 \mu A$
Emitter-Base Breakdown Voltage (Reverse Blocking)	BV_{ECV}	6	8.1	_	V	$I_C = 1\mu A$; 0.3V > V_{BC} > -6V
Collector Cutoff Current	I _{CBO}	_	<10	100	nA	V _{CB} = 450V
Emitter Cutoff Current	I _{EBO}	_	<10	100	nA	V _{EB} = 5.6V
Collector Emitter Cutoff Current	I _{CES}	_	<10	100	nA	V _{CE} = 450V
Static Forward Current Transfer Ratio (Note 10)	h	50	120	_		I _C = 30mA, V _{CE} = 10V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	_	70	_		I _C = 50mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	60	75	mV	$I_C = 20$ mA, $I_B = 2$ mA
Concolor Enniter Cutaration Voltage (Note 10)		_	70	90	mV	$I_C = 50$ mA, $I_B = 6$ mA
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	_	0.71	0.9	V	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	_	0.76	0.9	V	$I_C = 50$ mA, $I_B = 5$ mA
Output Capacitance	C_{obo}	_	_	5	pF	V _{CB} = 20V, f = 1MHz
Transition Frequency	f _T	50	_	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 20MHz
Turn-On Time	t _{on}	_	113	_	ns	V _C = 100V, I _C = 50mA
Turn-Off Time	t _{off}		3450		ns	I _{B1} = 5mA, I _{B2} = -10mA

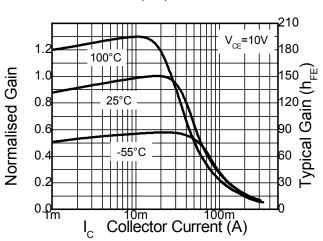
Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

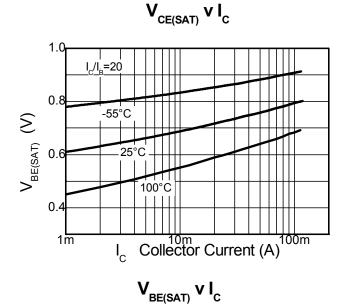


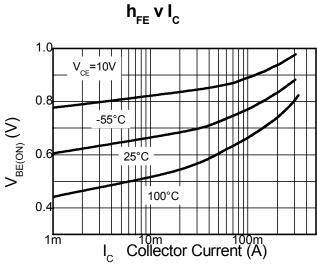
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







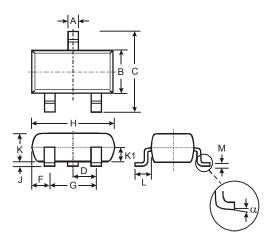






Package Outline Dimensions

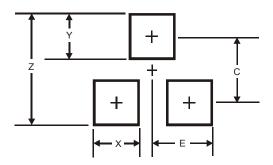
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.9			
X	0.8			
Υ	0.9			
С	2.0			
Е	1.35			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between Terminals.





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